Preferred Device

Triacs

Silicon Bidirectional Thyristors

Designed primarily for full wave ac control applications, such as motor controls, heating controls or dimmers; or wherever full—wave, silicon gate—controlled devices are needed.

- High Commutating di/dt and High Immunity to dv/dt @ 125°C
- Minimizes Snubber Networks for Protection
- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS
- High Surge Current Capability 150 Amperes
- Industry Standard TO-220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity
- Operational in Three Quadrants, Q1, Q2, and Q3
- Device Marking: Logo, Device Type, e.g., MAC16CD, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|--|---------------------|-------------------|--------------------|
| Peak Repetitive Off-State Voltage ⁽¹⁾ (T _J = -40 to 125°C) MAC16CD MAC16CM MAC16CN | VDRM, VRRM | 400 600 800 | Volts |
| On-State RMS Current (Full Cycle Sine Wave 50 to 60 Hz; T _C = 80°C) | I _{T(RMS)} | 16 | A |
| Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, TJ = 125°C) | ITSM | 150 | А |
| Circuit Fusing Consideration (t = 8.33 ms) | I ² t | 93 | A ² sec |
| Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 80°C) | PGM | 20 | Watts |
| Average Gate Power (t = 8.3 ms, T _C = 80°C) | PG(AV) | 0.5 | Watts |
| Operating Junction Temperature Range | TJ | -40 to +125 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |

⁽¹⁾ V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



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TRIACS 16 AMPERES RMS 400 thru 800 VOLTS





TO-220AB CASE 221A STYLE 4

| PIN ASSIGNMENT | | | | |
|-------------------|-----------------|--|--|--|
| 1 Main Terminal 1 | | | | |
| 2 | Main Terminal 2 | | | |
| 3 | Gate | | | |
| 4 | Main Terminal 2 | | | |

ORDERING INFORMATION

| Device | Package | Shipping |
|---------|---------|---------------|
| MAC16CD | TO220AB | 50 Units/Rail |
| MAC16CM | TO220AB | 50 Units/Rail |
| MAC16CN | TO220AB | 50 Units/Rail |

Preferred devices are recommended choices for future use and best overall value.



THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|--|-------------|------|
| Thermal Resistance — Junction to Case — Junction to Ambient | R _θ JC R _θ JA | 2.2 62.5 | °C/W |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds | TL | 260 | °C |

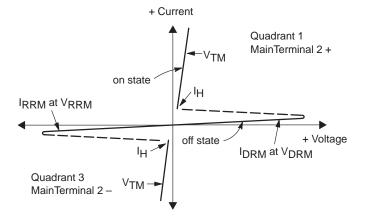
ELECTRICAL CHARACTERISTICS (T_{.1} = 25°C unless otherwise noted; Electricals apply in both directions)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|----------------------|-------------------|-------------------|-------------------|------|
| OFF CHARACTERISTICS | | | | | • |
| Peak Repetitive Blocking Current (V_D = Rated V_{DRM} , V_{RRM} Gate Open) $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$ | IDRM, IRRM | _ _ | _ _ | 0.01 2.0 | mA |
| ON CHARACTERISTICS | | | | | |
| Peak On-State Voltage(1) (I _{TM} = ±21 A Peak) | V _{TM} | _ | 1.2 | 1.6 | V |
| Gate Trigger Current (Continuous dc) $ (V_D = 12 \ V, \ R_L = 100 \ \Omega) $ $ MT2(+), \ G(+) $ $ MT2(+), \ G(-) $ $ MT2(-), \ G(-) $ | I _{GT} | 8.0 8.0 8.0 | 12 16 20 | 35 35 35 | mA |
| Holding Current ($V_D = 12 \text{ V}$, Gate Open, Initiating Current = $\pm 150 \text{ mA}$) | lΗ | _ | 20 | 50 | mA |
| Latching Current ($V_D = 12 \text{ V}, I_G = 35 \text{ mA}$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) | IL | _ _ _ | 25 40 24 | 50 80 50 | mA |
| Gate Trigger Voltage (Continuous dc) $ (V_D = 12 \ V, \ R_L = 100 \ \Omega) $ $ MT2(+), \ G(+) $ $ MT2(+), \ G(-) $ $ MT2(-), \ G(-) $ | VGT | 0.5 0.5 0.5 | .75 .72 .82 | 1.5 1.5 1.5 | V |
| DYNAMIC CHARACTERISTICS | | | | | |
| Rate of Change of Commutating Current ($V_D = 400 \text{ V}$, $I_{TM} = 6.0 \text{ A}$, Commutating dv/dt = 24 V/ μ s, Gate Open, $I_J = 125 ^{\circ}\text{C}$, $I_$ | (di/dt) _C | 15 | _ | _ | A/ms |
| Critical Rate of Rise of Off-State Voltage (VD = Rated VDRM, Exponential Waveform, Gate Open, TJ = 125°C) | | 600 | _ | _ | V/µs |
| Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 µsec; diG/dt = 200 mA/µsec; f = 60 Hz | di/dt | _ | _ | 10 | A/μs |

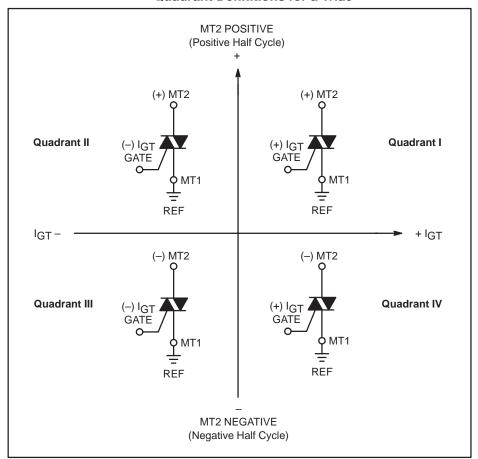
⁽¹⁾ Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Voltage Current Characteristic of Triacs (Bidirectional Device)

| Symbol | Parameter |
|-----------------|---|
| VDRM | Peak Repetitive Forward Off State Voltage |
| IDRM | Peak Forward Blocking Current |
| VRRM | Peak Repetitive Reverse Off State Voltage |
| IRRM | Peak Reverse Blocking Current |
| V _{TM} | Maximum On State Voltage |
| lΗ | Holding Current |



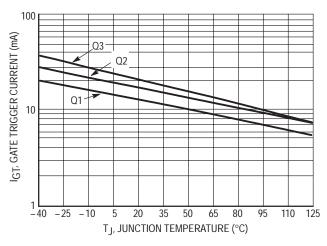
Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

1.10

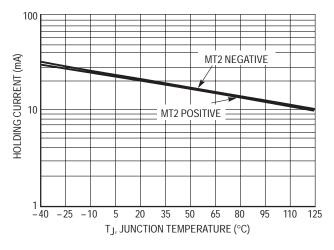


VGT, GATE TRIGGER VOLTAGE (VOLT) 1.00 0.90 Q1 0.80 0.70 0.60 0.50 0.40 40 -25 80 -10 20 35 50 65 125 T_J, JUNCTION TEMPERATURE (°C)

Q3

Figure 1. Typical Gate Trigger Current versus Junction Temperature

Figure 2. Typical Gate Trigger Voltage versus Junction Temperature



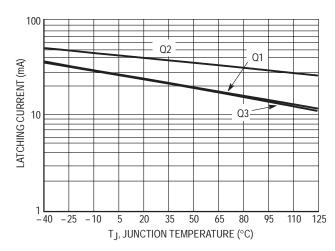
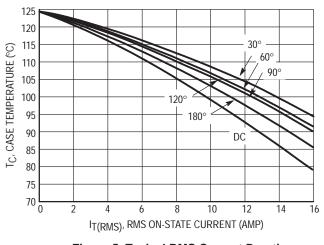


Figure 3. Typical Holding Current versus Junction Temperature

Figure 4. Typical Latching Current versus Junction Temperature



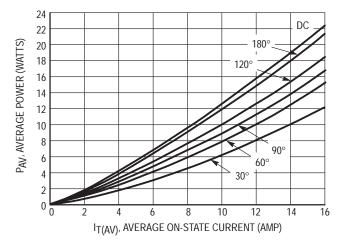


Figure 5. Typical RMS Current Derating

Figure 6. On-State Power Dissipation

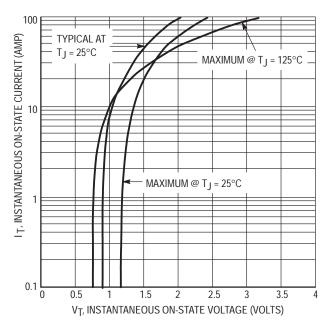


Figure 7. On-State Characteristics

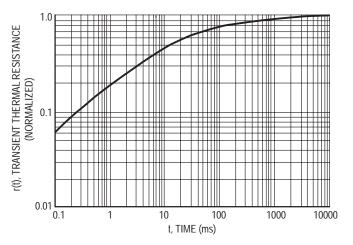
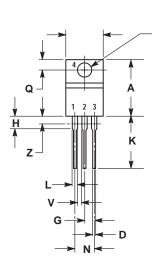
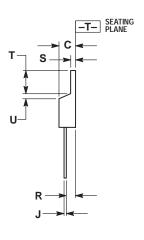


Figure 8. Typical Thermal Response

PACKAGE DIMENSIONS

TO-220AB CASE 221A-09 ISSUE Z





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.570 | 0.620 | 14.48 | 15.75 |
| В | 0.380 | 0.405 | 9.66 | 10.28 |
| С | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| Н | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | | 1.15 | |
| Z | | 0.080 | | 2.04 |

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

Notes

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